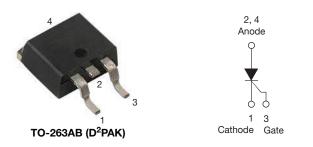
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Thyristor Surface Mount Phase Control SCR, 16 A



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PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
Diode variation	Single SCR							
I _{T(AV)}	10 A							
V _{DRM} /V _{RRM}	1600 V							
V _{TM}	1.4 V							
I _{GT}	60 mA							
TJ	-40 °C to 125 °C							

FEATURES

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- Designed and qualified according JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

DESCRIPTION

The VS-16TTS16SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5						
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5						

Note

• $T_A = 55 \ ^\circ C$, $T_J = 125 \ ^\circ C$, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	10	Δ.						
I _{RMS}		16							
V _{RRM} /V _{DRM}		1600	V						
I _{TSM}		200	A						
V _T	10 A, T _J = 25 °C	1.4	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to 125	°C						

VOLTAGE RATINGS										
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA							
VS-16TTS16SPbF	1600	1600	10							

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PARAMETER	SYMBOL		TEST CONDITIONS	VAL			
PARAMETER	STMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 18	0° conduction, half sine wave	1	0		
Maximum RMS on-state current	I _{RMS}			1	6	А	
Maximum peak, one-cycle,	1	10 ms sine pu	se, rated V _{RRM} applied	17	70	A	
non-repetitive surge current	I _{TSM}	10 ms sine pu	se, no voltage reapplied	20	00		
Maximum I ² t for fusing	l ² t	10 ms sine pu	se, rated V _{RRM} applied	144		A ² s	
Maximum intronusing	1-1	10 ms sine pu	200		A-5		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 1	0 ms, no voltage reapplied	2000		A²√s	
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °	C	1.4		V	
On-state slope resistance	r _t	T 105 %C		24.0		mΩ	
Threshold voltage	V _{T(TO)}	1J=125 C	T _J = 125 °C		.1	V	
Maximum reverse and direct lackage surrent	1 /1	T _J = 25 °C		0.5			
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10			
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		100	150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C			200		
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max. li	near to 80 % V _{DRM} = Rg - k = Open	Dpen 500		V/µs	
Maximum rate of rise of turned-on current	dl/dt			150		A∕µs	

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	vv				
Maximum peak positive gate current	+ I _{GM}		1.5	А				
Maximum peak negative gate voltage	- V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T_J = - 10 °C	90	mA				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	60					
		Anode supply = 6 V, resistive load, T_J = 125 °C	35					
		Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0					
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V				
Maximum DC gate voltage not to trigger	V _{GD}		0.25	1				
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T 105 %	4	μs				
Typical turn-off time	tq	T _J = 125 °C	110					

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THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C/W			
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount ⁽¹⁾	40	0/11			
Approvingete weight			2	g			
Approximate weight			0.07	oz.			
Marking device		Case style D ² PAK (SMD-220)	16TTS	16S			

Note

⁽¹⁾ When mounted on 1 " square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994.

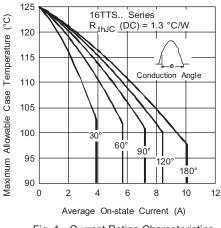


Fig. 1 - Current Rating Characteristics

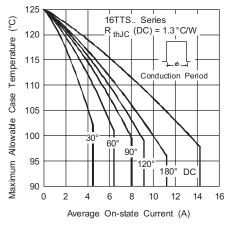


Fig. 2 - Current Rating Characteristics

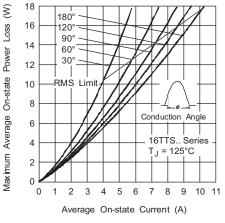


Fig. 3 - On-State Power Loss Characteristics

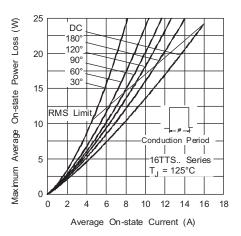


Fig. 4 - On-State Power Loss Characteristics

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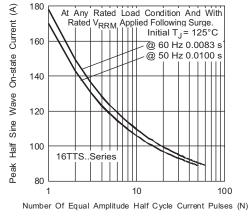
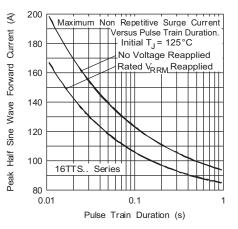
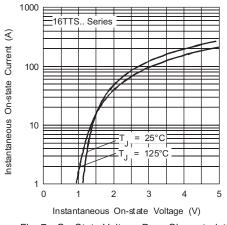


Fig. 5 - Maximum Non-Repetitive Surge Current









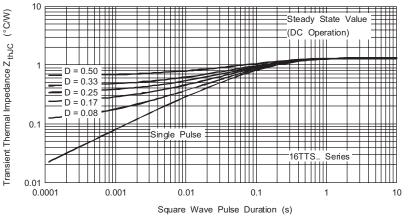
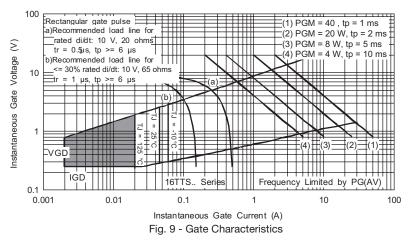


Fig. 8 - Thermal Impedance ZthJC Characteristics

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ORDERING INFORMATION TABLE

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Device code	VS-	16	т	т	S	16	S	TRL	PbF		
	1	2	3	4	5	6	7	8	9		
	1 -	- Visł	nay Sem	niconduc	ctors pro	oduct					
	2	2 - Current rating									
	3.										
		T =	T = single thyristor								
	4	- Pac	kage:								
		T =	TO-220	AC							
	5	- Тур	e of silio	con:							
		S =	standar	d recov	ery recti	ifier					
	6 ·	- Vol	tage rati	ng: Volt	age cod	e x 100	= V _{RRI}	_M (16 = 1	1600 V)		
	7.	- S=	TO-220	D ² PAK	(SMD-	220) ve	rsion				
	8 -	• No	one = tu	be							
		• TF	RL = tap	e and re	el (left o	oriented)				
		• TF	RR = tap	e and re	eel (righ	t oriente	ed)				
	9.	- PbF	= lead	(Pb)-fre	е						

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-16TTS16SPbF	50	1000	Antistatic plastic tubes						
VS-16TTS16STRRPbF	800	800	13" diameter reel						
VS-16TTS16STRLPbF	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						

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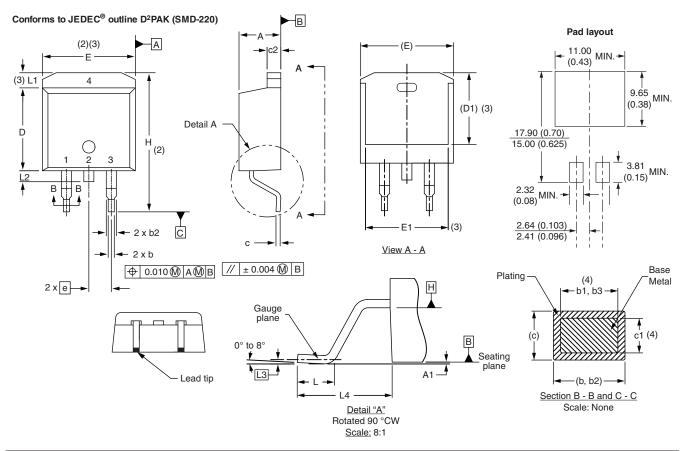
Outline Dimensions



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25 BSC		0.25 BSC 0.010 BSC		
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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